

TPCF8306

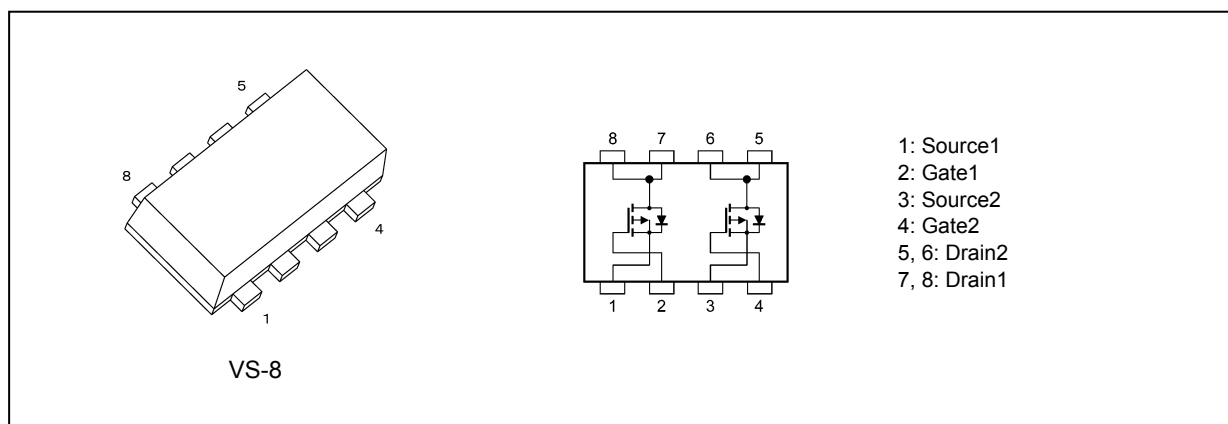
1. Applications

- Power Management Switches

2. Features

- (1) Small footprint due to a small and thin package
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 90 \text{ m}\Omega$ (typ.) ($V_{GS} = -4.5 \text{ V}$)
- (3) Low leakage current: $I_{DSS} = -10 \text{ }\mu\text{A}$ (max) ($V_{DS} = -30 \text{ V}$)
- (4) Enhancement mode: $V_{th} = -0.8$ to -2.0 V ($V_{DS} = -10 \text{ V}$, $I_D = -0.1 \text{ mA}$)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	-30	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	-30	
Gate-source voltage	V_{GSS}	-25/+20	
Drain current (DC) (Note 1)	I_D	-3.2	A
Drain current (pulsed) (Note 1)	I_{DP}	-12.8	
Power dissipation (single operation) ($t = 5 \text{ s}$) (Note 2), (Note 4)	$P_{D(1)}$	1.35	W
Power dissipation (per device for dual operation) ($t = 5 \text{ s}$) (Note 2), (Note 5)	$P_{D(2)}$	1.12	
Power dissipation (single operation) ($t = 5 \text{ s}$) (Note 3), (Note 4)	$P_{D(1)}$	0.53	
Power dissipation (per device for dual operation) ($t = 5 \text{ s}$) (Note 3), (Note 5)	$P_{D(2)}$	0.33	
Single-pulse avalanche energy (Note 6)	E_{AS}	2.6	mJ
Avalanche current	I_{AR}	-3.2	A
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

2011-09

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-ambient thermal resistance (single operation) (t = 5 s) (Note 2), (Note 4)	$R_{th(ch-a)(1)}$	92.6	°C/W
Channel-to-ambient thermal resistance (per device for dual operation) (t = 5 s) (Note 2), (Note 5)	$R_{th(ch-a)(2)}$	111.6	
Channel-to-ambient thermal resistance (single operation) (t = 5 s) (Note 3), (Note 4)	$R_{th(ch-a)(1)}$	235.8	
Channel-to-ambient thermal resistance (per device for dual operation) (t = 5 s) (Note 3), (Note 5)	$R_{th(ch-a)(2)}$	378.8	

Note 1: Ensure that the channel temperature does not exceed 150°C.

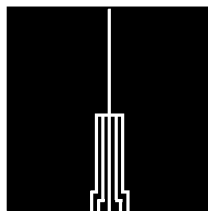
Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: Power dissipation and thermal resistance values per device with the other device being off (During single operation, power is supplied to only one of the two devices.)

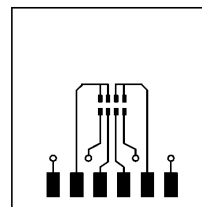
Note 5: Power dissipation and thermal resistance values per device for dual operation (During dual operation, power is evenly supplied to both devices.)

Note 6: $V_{DD} = -24\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 0.2\text{ mH}$, $R_G = 25\ \Omega$, $I_{AR} = -3.2\text{ A}$



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 0.1	μA
Drain cut-off current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$	—	—	-10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = -10\text{ mA}, V_{GS} = 0\text{ V}$	-30	—	—	V
Drain-source breakdown voltage (Note 7)	$V_{(BR)DSX}$	$I_D = -10\text{ mA}, V_{GS} = 10\text{ V}$	-21	—	—	
Gate threshold voltage	V_{th}	$V_{DS} = -10\text{ V}, I_D = -0.1\text{ mA}$	-0.8	—	-2.0	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = -4.5\text{ V}, I_D = -1.6\text{ A}$	—	90	120	$\text{m}\Omega$
		$V_{GS} = -10\text{ V}, I_D = -1.6\text{ A}$	—	60	72	

Note 7: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	390	—	pF
Reverse transfer capacitance	C_{rss}		—	65	—	
Output capacitance	C_{oss}		—	85	—	
Switching time (rise time)	t_r	See Figure 6.2.1	—	9.0	—	ns
Switching time (turn-on time)	t_{on}		—	15	—	
Switching time (fall time)	t_f		—	6.7	—	
Switching time (turn-off time)	t_{off}		—	38	—	

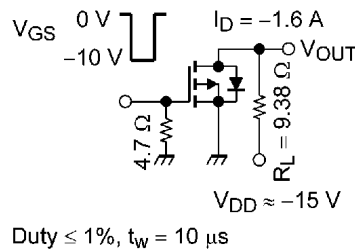


Fig. 6.2.1 Switching Time Test Circuit

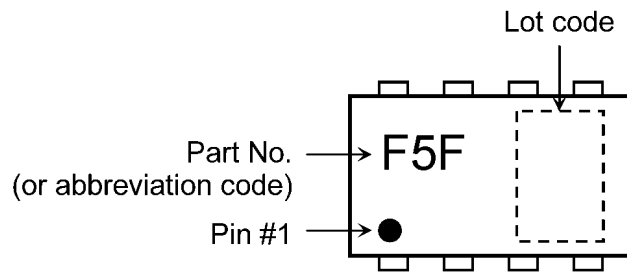
6.3. Gate Charge Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx -24\text{ V}, V_{GS} = -10\text{ V}, I_D = -3.2\text{ A}$	—	10	—	nC
Gate-source charge 1	Q_{gs1}		—	1.0	—	
Gate-drain charge	Q_{gd}		—	3.3	—	

6.4. Source-Drain Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (pulsed) (Note 8)	I_{DRP}	—	—	—	-12.8	A
Diode forward voltage	V_{DSF}	$I_{DR} = -3.2\text{ A}, V_{GS} = 0\text{ V}$	—	—	1.2	V

Note 8: Ensure that the channel temperature does not exceed 150°C .

7. Marking**Fig. 7.1 Marking**

8. Characteristics Curves (Note)

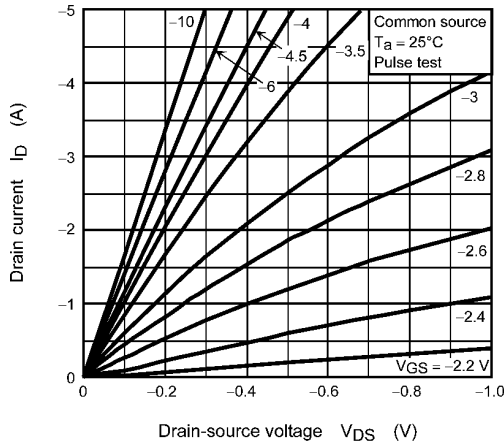


Fig. 8.1 $I_D - V_{DS}$

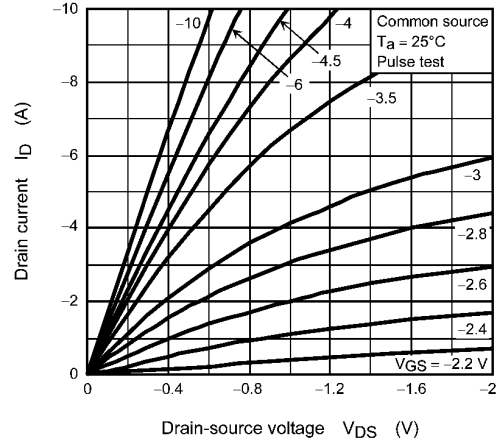


Fig. 8.2 $I_D - V_{DS}$

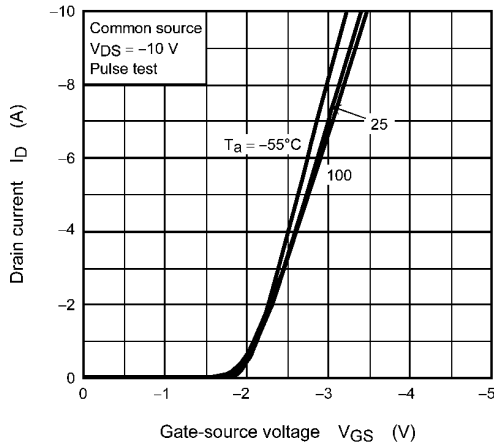


Fig. 8.3 $I_D - V_{GS}$

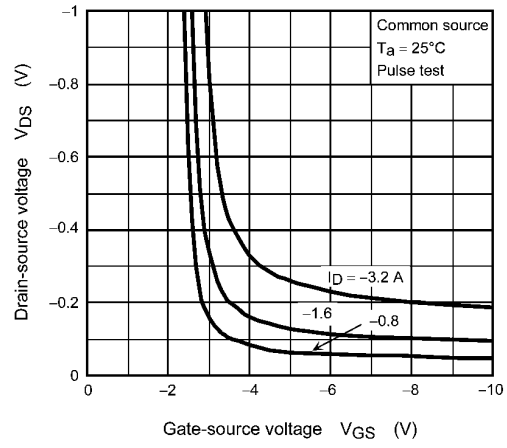


Fig. 8.4 $V_{DS} - V_{GS}$

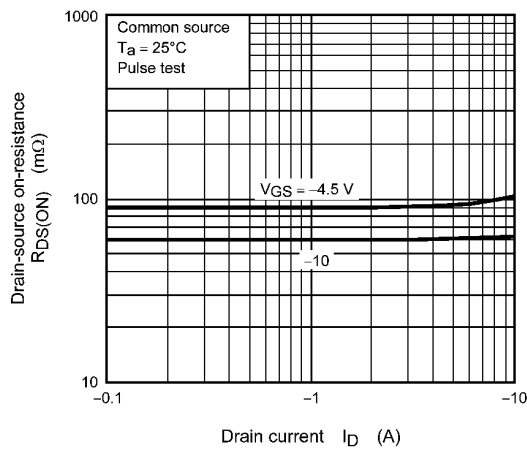


Fig. 8.5 $R_{DS(ON)} - I_D$

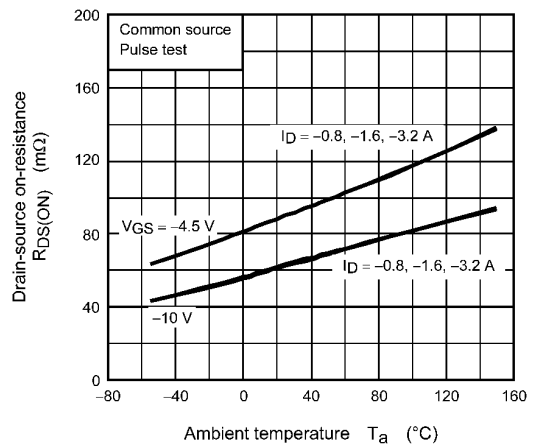


Fig. 8.6 $R_{DS(ON)} - T_a$

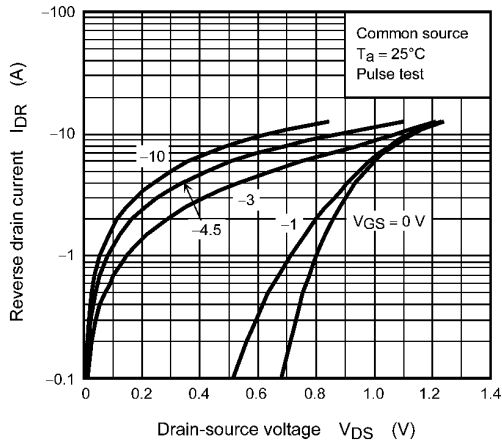


Fig. 8.7 $I_{DR} - V_{DS}$

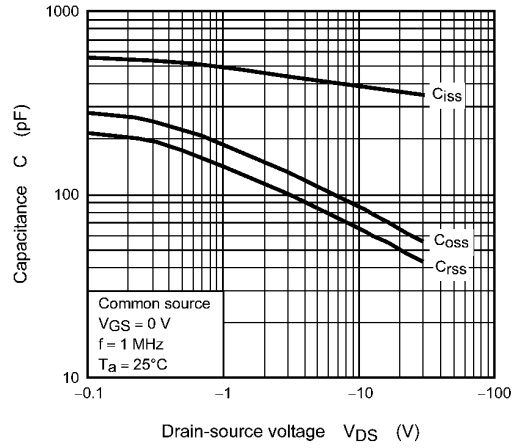


Fig. 8.8 Capacitance - V_{DS}

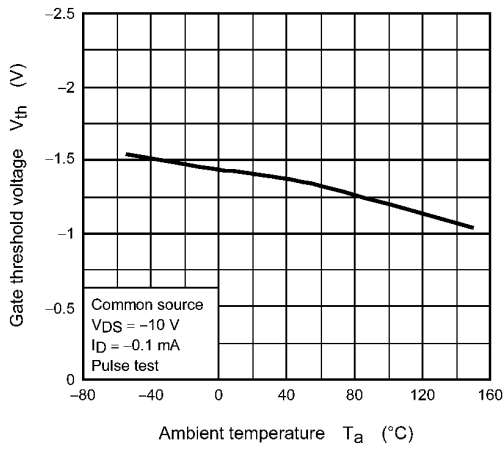


Fig. 8.9 $V_{th} - T_a$

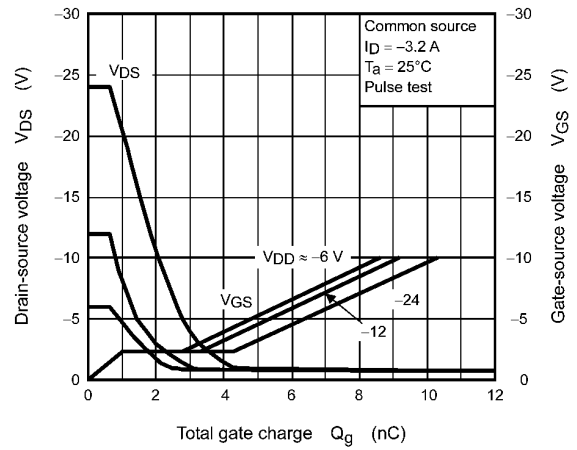
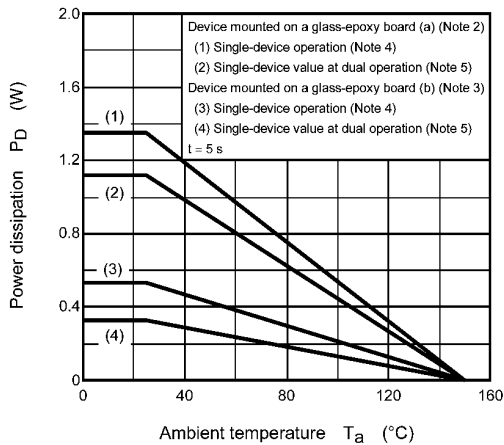


Fig. 8.10 Dynamic Input/Output Characteristics



**Fig. 8.11 $P_D - T_a$
 (Guaranteed Maximum)**

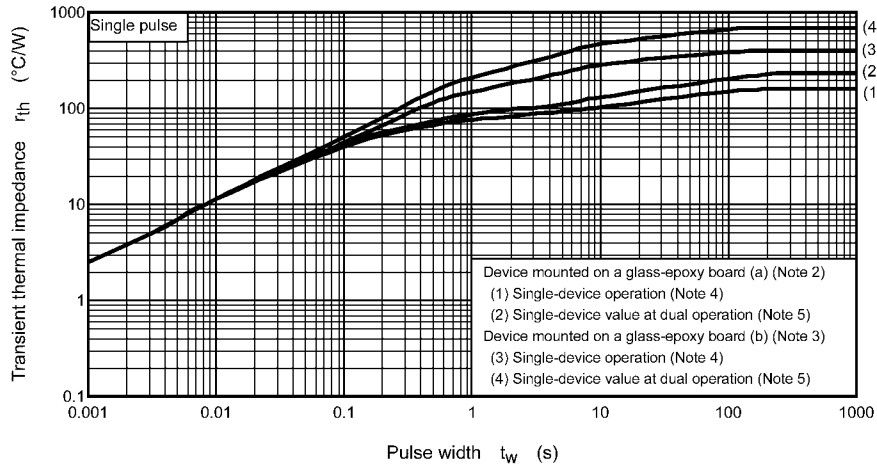


Fig. 8.12 $r_{th} - t_w$
(Guaranteed Maximum)

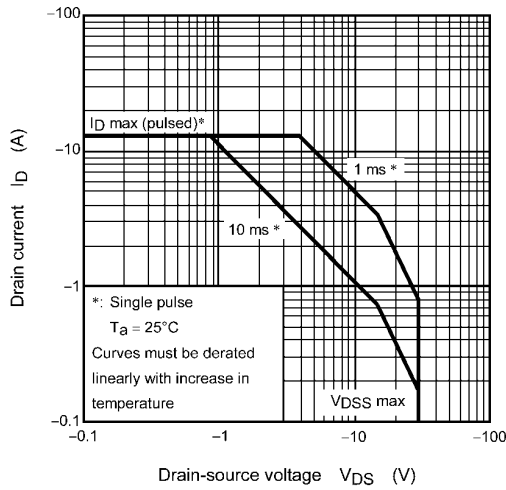
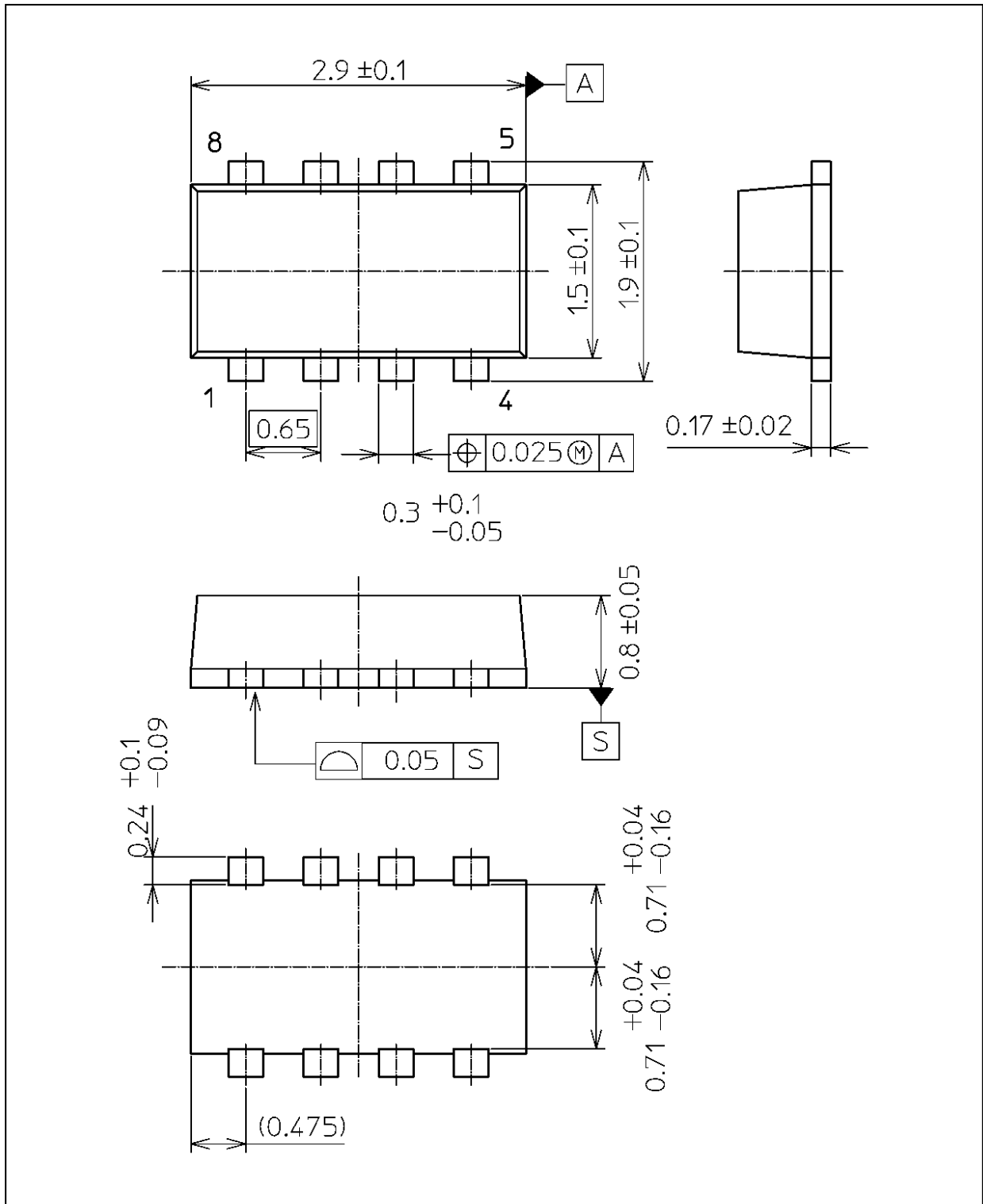


Fig. 8.13 Safe Operating Area
(Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.011 g (typ.)

Package Name(s)
TOSHIBA: 2-3U1S
Nickname: VS-8

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